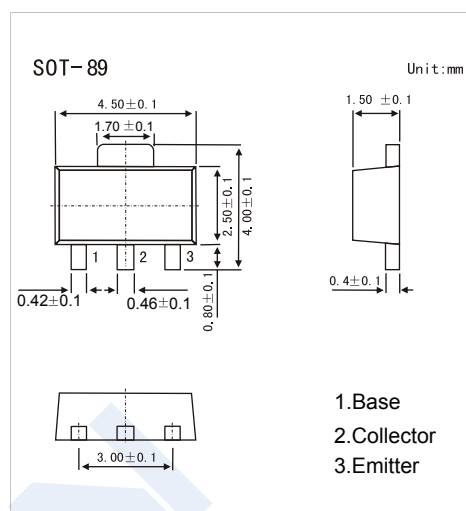


## PNP Transistors

## 2SB772

## ■ Features

- PNP transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SD882

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CB0}$	-40	V
Collector to Emitter Voltage	$V_{CEO}$	-30	V
Emitter to Base Voltage	$V_{EBO}$	-6	V
Collector Current to Continuous	$I_C$	-3	A
Collector Dissipation	$P_c$	0.5	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

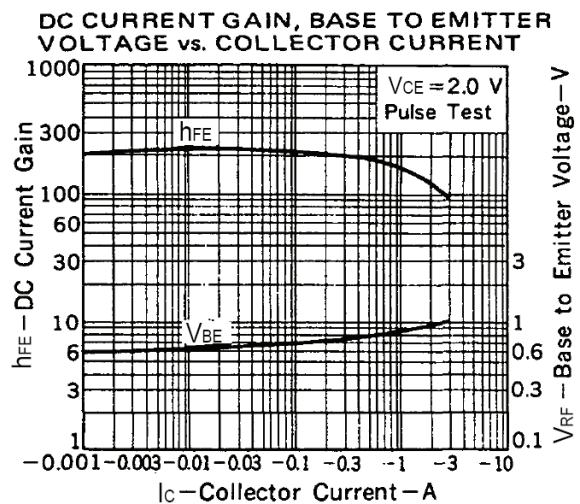
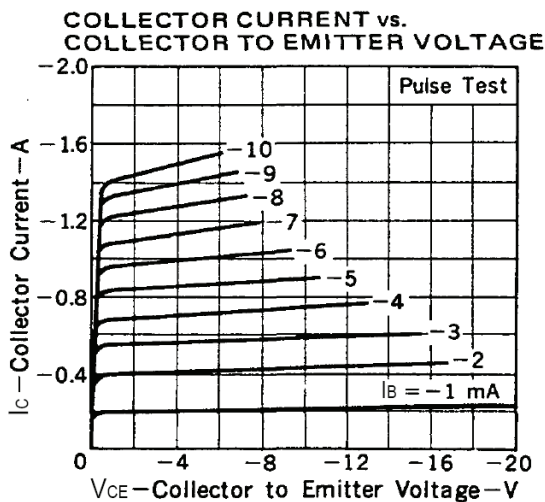
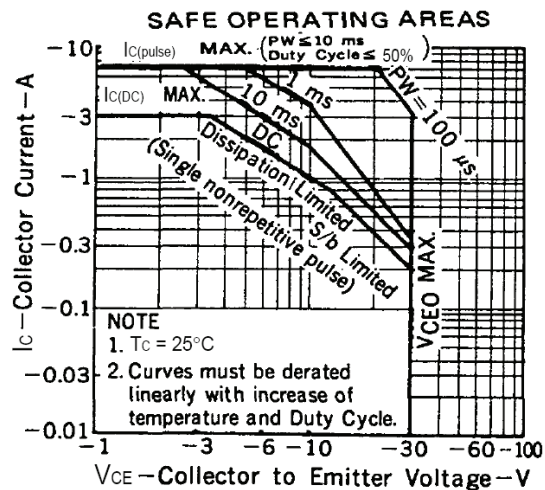
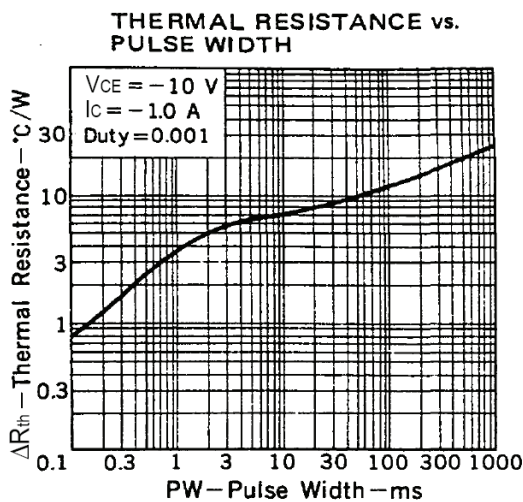
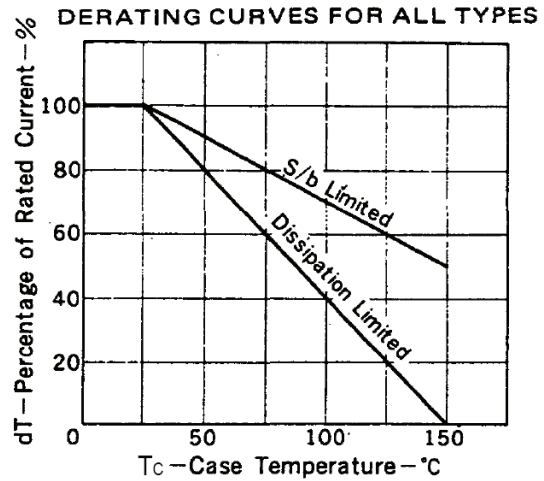
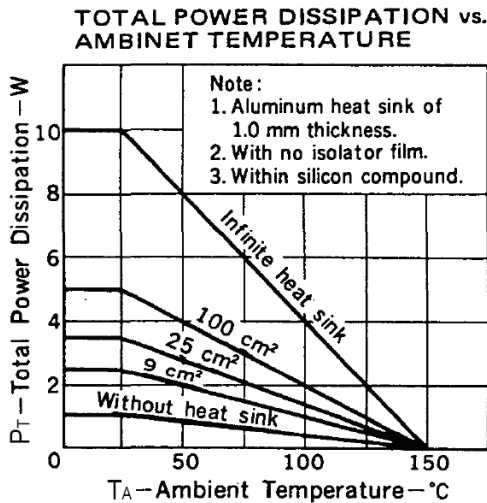
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CB0}$	$I_C = -100\mu\text{A}, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40\text{ V}, I_E = 0$			-1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6\text{ V}, I_C = 0$			-1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -2\text{V}, I_C = -1\text{A}$	60		400	
		$V_{CE} = -2\text{V}, I_C = -100\text{mA}$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{A}, I_B = -0.2\text{A}$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{mA}, f = 10\text{MHz}$	50			MHz

■ Classification of  $h_{FE}(1)$ 

Marking	772*			
Range	R	Q	P	E
$h_{FE}$	60~120	100~200	160~320	200~400

2SB772

Typical Characteristics



2SB772

